

PATENT CLAIMS (amended on 01.06.2005)

1. A power semiconductor module comprising
 - at least one semiconductor chip (11) made of a semiconductor material and having a first and a second main electrode,
 - a first and second main connection (91, 92),
 - a contact lamina (2) in electrical contact with the first main electrode and the first main connection (92),
 - the contact lamina (2) containing an alloying partner and it being possible for a eutectic to be formed between the alloying partner and the semiconductor material,
 - 15 - the contact lamina being coated with an electrically conductive protective layer (31, 32), characterized in that
 - the protective layer (31, 32) has at least one electrically conductive base layer (31) applied on the contact lamina (2), and
 - an electrically conductive surface layer (32), which forms the external contact area,
 - and in that
 - the base layer and the surface layer substantially comprise different materials.
2. The power semiconductor module as claimed in claim 1, characterized in that
 - the base layer (31) substantially comprises Ni and preferably has a thickness of between approximately 1 μm and 15 μm , preferably between 2 μm and 8 μm .
3. The power semiconductor module as claimed in claim 1 or 2, characterized in that
 - the surface layer (32) has a thickness of between approximately 0.1 μm and 5 μm .

- 11 -

4. The power semiconductor module as claimed in one of claims 1 to 3, characterized in that

- the surface layer (32) substantially comprises Ru,
- an electrically conductive intermediate layer is provided between the surface layer (32) and the base layer (31), said intermediate layer substantially comprising Au and preferably having a thickness of approximately 0.2 μm , and
- the base layer (31) preferably has a thickness of between 5 μm and 12 μm .

5. The power semiconductor module as claimed in one of the preceding claims, characterized in that

- the semiconductor chip (11) internally has an IGBT structure or a diode structure.

6. The power semiconductor module as claimed in claim 1, characterized in that

- the base layer (31) comprises a good covering material, and in that
- the surface layer (32) comprises a material having one or more of the following properties:
 - a non-oxidizable, preferably exhibiting little chemical reactivity,
 - b does not react chemically with a first electrode metallization of the first main electrode and exhibits neither contact corrosion nor material diffusion,
 - c has a low coefficient of friction,
 - d can be deposited at temperatures at which the contact layer is not damaged or deformed.